

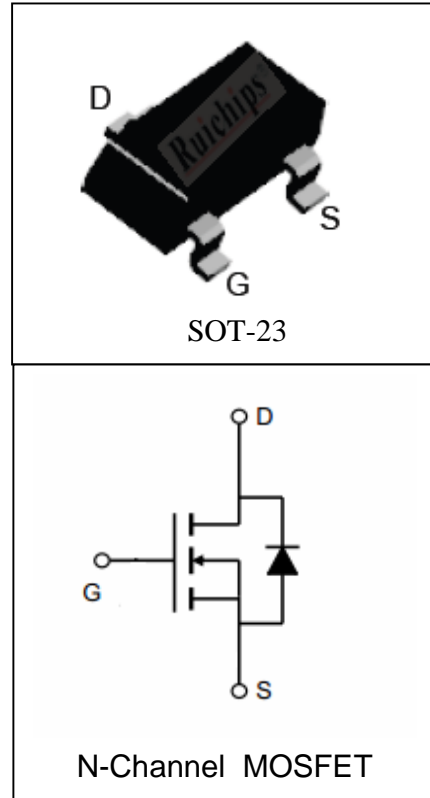
Features

- 30V/4A,
 $R_{DS(ON)} = 44m\Omega$ (Typ.) @ $V_{GS} = 4.5V$
 $R_{DS(ON)} = 53m\Omega$ (Typ.) @ $V_{GS} = 2.5V$
- Low $R_{DS(ON)}$
- Super High Dense Cell Design
- Reliable and Rugged
- Lead Free and Green Available

Applications

- Load/System Switch

Pin Description



Absolute Maximum Ratings

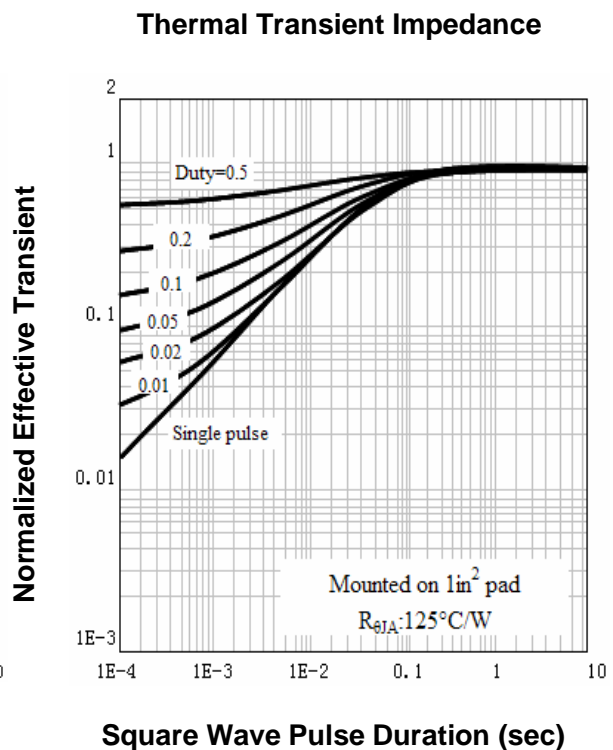
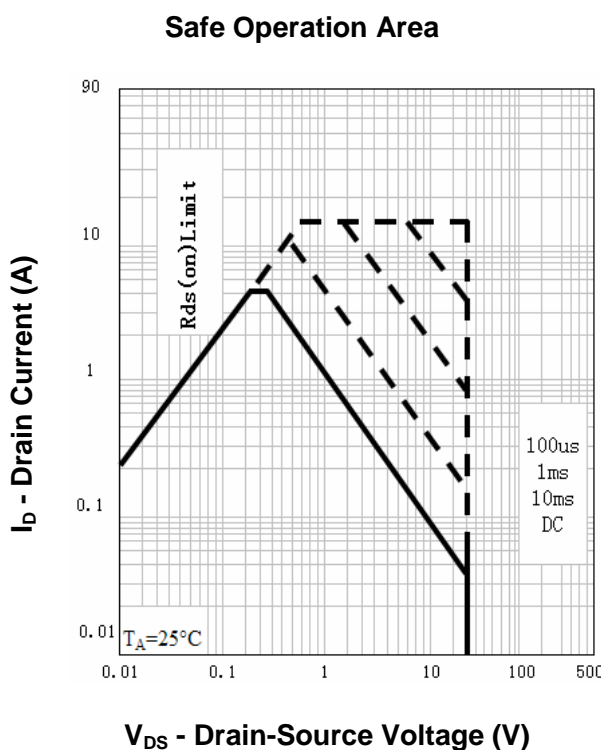
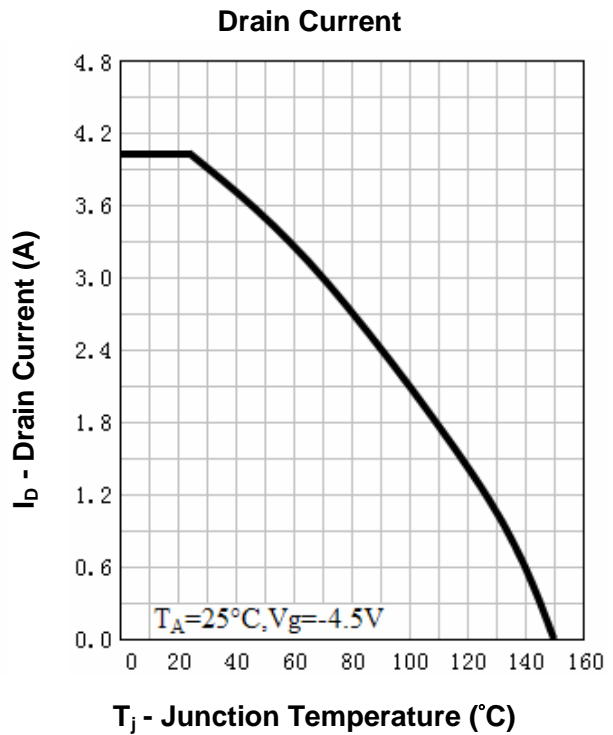
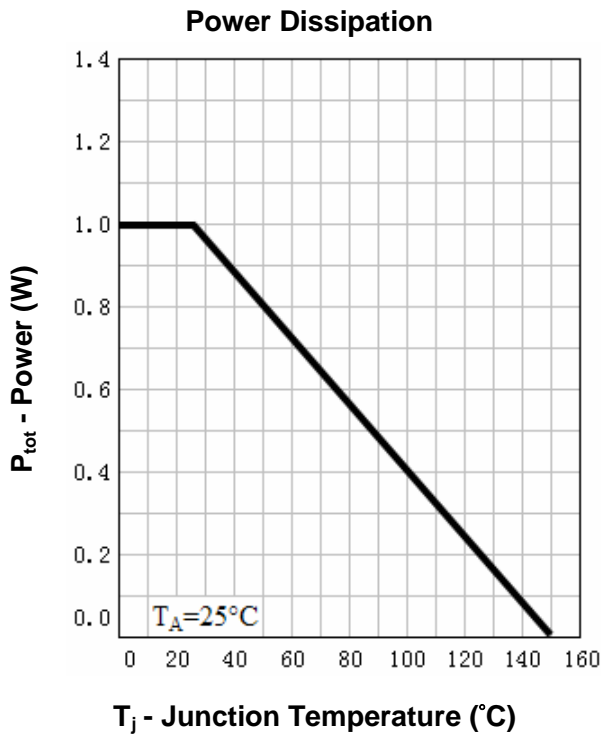
Symbol	Parameter	Rating	Unit
Common Ratings ($T_A = 25^\circ C$ Unless Otherwise Noted)			
V_{DSS}	Drain-Source Voltage	30	V
V_{GSS}	Gate-Source Voltage	± 12	
T_J	Maximum Junction Temperature	150	$^\circ C$
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
I_S	Diode Continuous Forward Current	$T_A = 25^\circ C$ 1.1	A
Mounted on Large Heat Sink			
I_{DP}	300 μs Pulse Drain Current Tested	$T_A = 25^\circ C$ 15 ^①	A
I_D	Continuous Drain Current ($V_{GS} = 4.5V$)	$T_A = 25^\circ C$ 4	A
		$T_A = 70^\circ C$ 2.9	
P_D	Maximum Power Dissipation	$T_A = 25^\circ C$ 1	W
		$T_A = 70^\circ C$ 0.64	
$R_{\theta JA}$ ^②	Thermal Resistance-Junction to Ambient	125	$^\circ C/W$

Electrical Characteristics (T_A=25°C Unless Otherwise Noted)

Symbol	Parameter	Test Condition	RU304B			Unit
			Min.	Typ.	Max.	
Static Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _{DS} =250μA	30			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =30V, V _{GS} =0V T _J =85°C			1	μA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =250μA	0.5	-	1.5	V
I _{GSS}	Gate Leakage Current	V _{GS} =±12V, V _{DS} =0V			±100	nA
R _{DS(ON)} ^③	Drain-Source On-state Resistance	V _{GS} =4.5V, I _{DS} =4A		44	60	mΩ
		V _{GS} =2.5V, I _{DS} =2A		53	80	mΩ
Diode Characteristics						
V _{SD} ^③	Diode Forward Voltage	I _{SD} =1A, V _{GS} =0V			1	V
t _{rr}	Reverse Recovery Time	I _{SD} =2A, dI _{SD} /dt=100A/μs		13		ns
Q _{rr}	Reverse Recovery Charge			4		nC
Dynamic Characteristics ^④						
R _G	Gate Resistance	V _{GS} =0V, V _{DS} =0V, F=1MHz		0.8		Ω
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =15V, Frequency=1.0MHz		210		pF
C _{oss}	Output Capacitance			32		
C _{rss}	Reverse Transfer Capacitance			19		
t _{d(ON)}	Turn-on Delay Time	V _{DD} =15V, R _L =7.5Ω, I _{DS} =2A, V _{GEN} =4.5V, R _G =1Ω		6		ns
t _r	Turn-on Rise Time			10		
t _{d(OFF)}	Turn-off Delay Time			15		
t _f	Turn-off Fall Time			7		
Gate Charge Characteristics ^④						
Q _g	Total Gate Charge	V _{DS} =24V, V _{GS} =4.5V, I _{DS} =2A		4		nC
Q _{gs}	Gate-Source Charge			0.5		
Q _{gd}	Gate-Drain Charge			1.2		

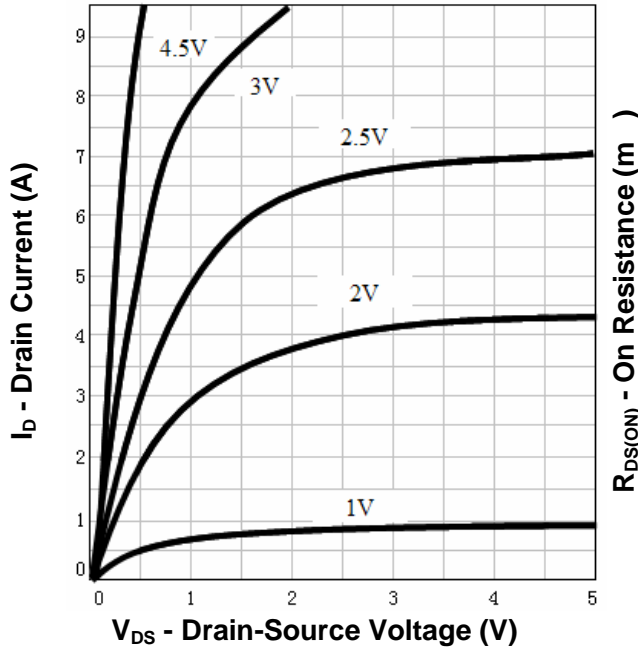
- Notes: ① Pulse width limited by safe operating area.
 ② When mounted on 1 inch square copper board, t ≤ 10sec. The value in any given application depends on the user's specific board design.
 ③ Pulse test ; Pulse width ≤ 300μs, duty cycle ≤ 2%.
 ④ Guaranteed by design, not subject to production testing.

Typical Characteristics

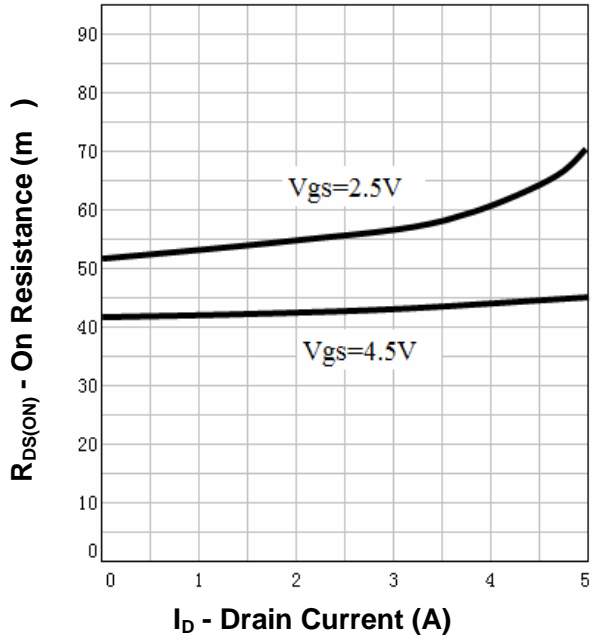


Typical Characteristics

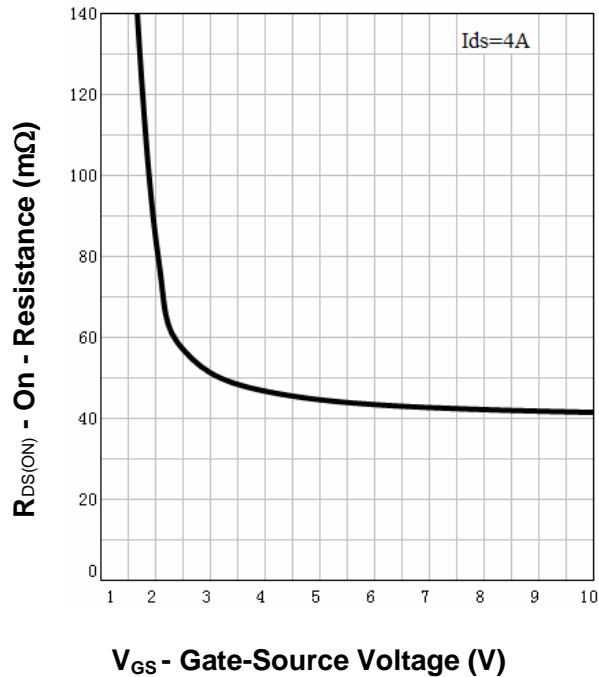
Output Characteristics



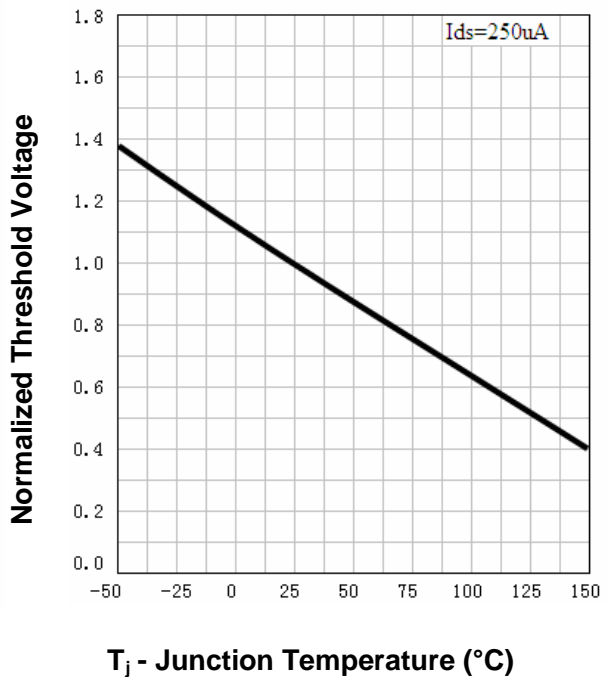
Drain-Source On Resistance



Drain-Source On Resistance

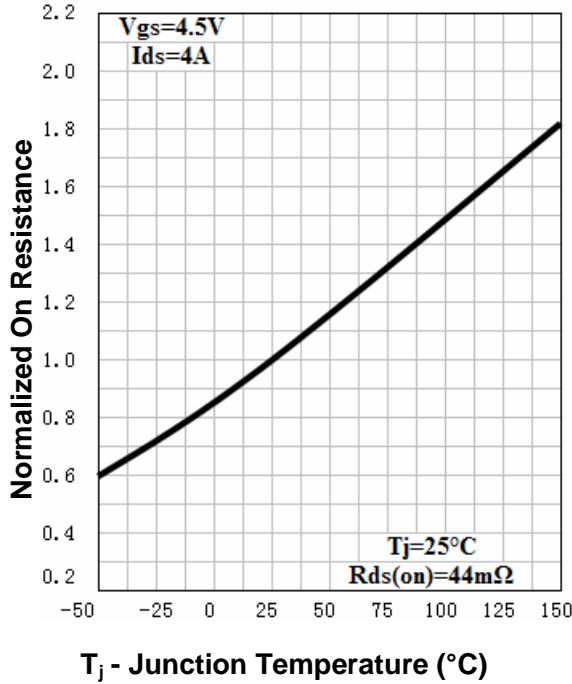


Gate Threshold Voltage

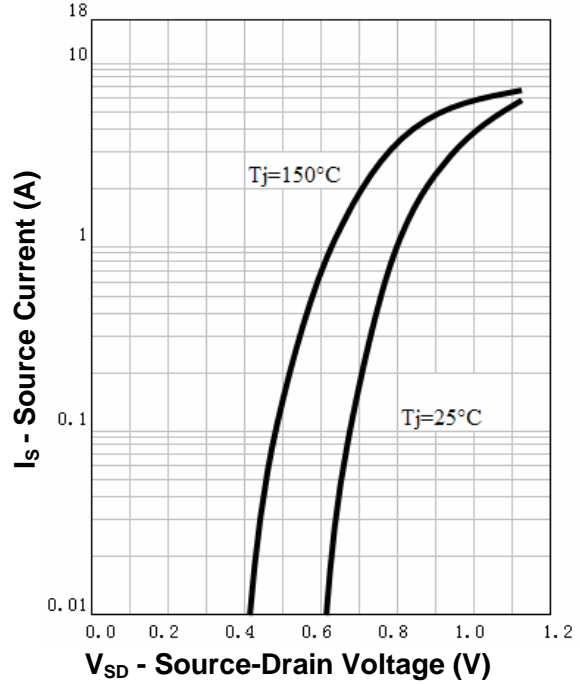


Typical Characteristics

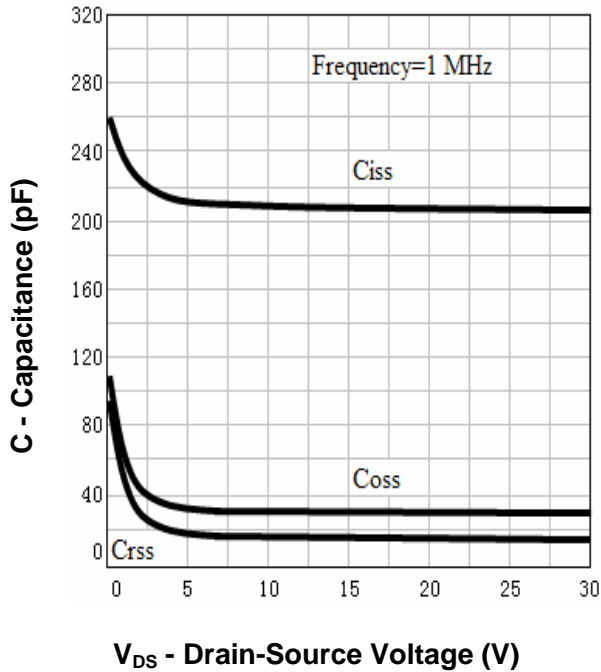
Drain-Source On Resistance



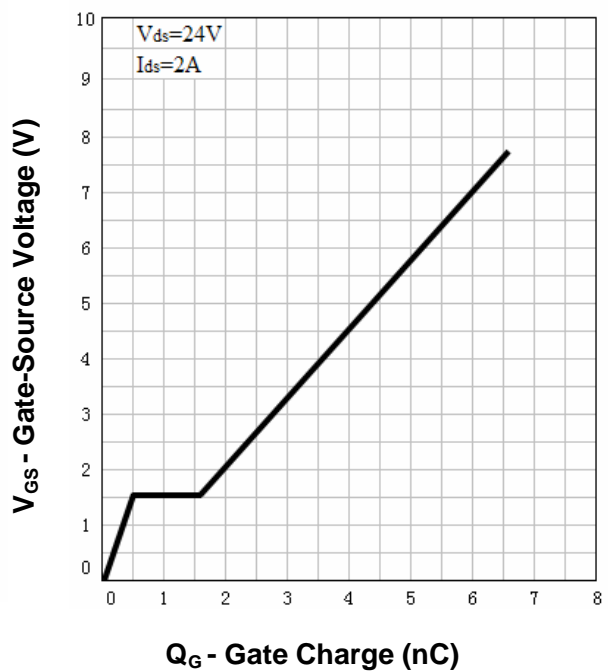
Source-Drain Diode Forward



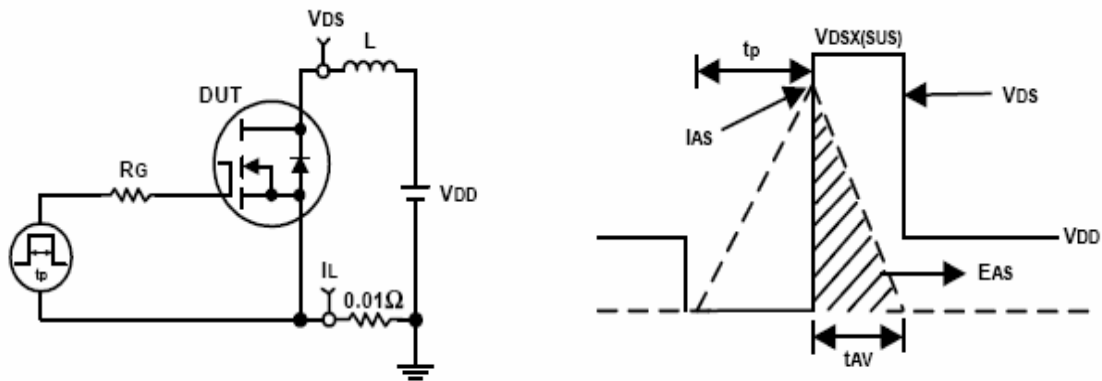
Capacitance



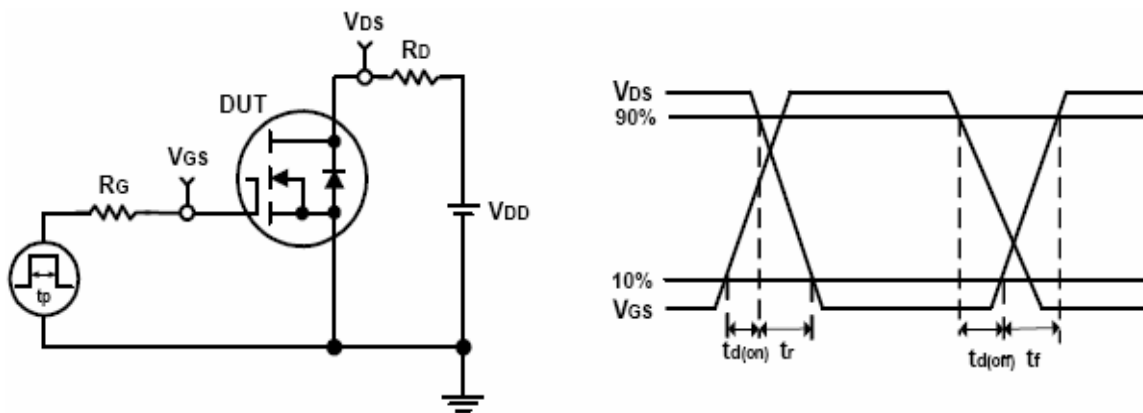
Gate Charge



Avalanche Test Circuit and Waveforms



Switching Time Test Circuit and Waveforms



Ordering and Marking Information

Device	Marking ^①	Package	Packaging	Quantity	Reel Size	Tape width
RU304B	6XYWW	SOT-23	Tape&Reel	3000	7''	8mm

① The following characters could be different and means:

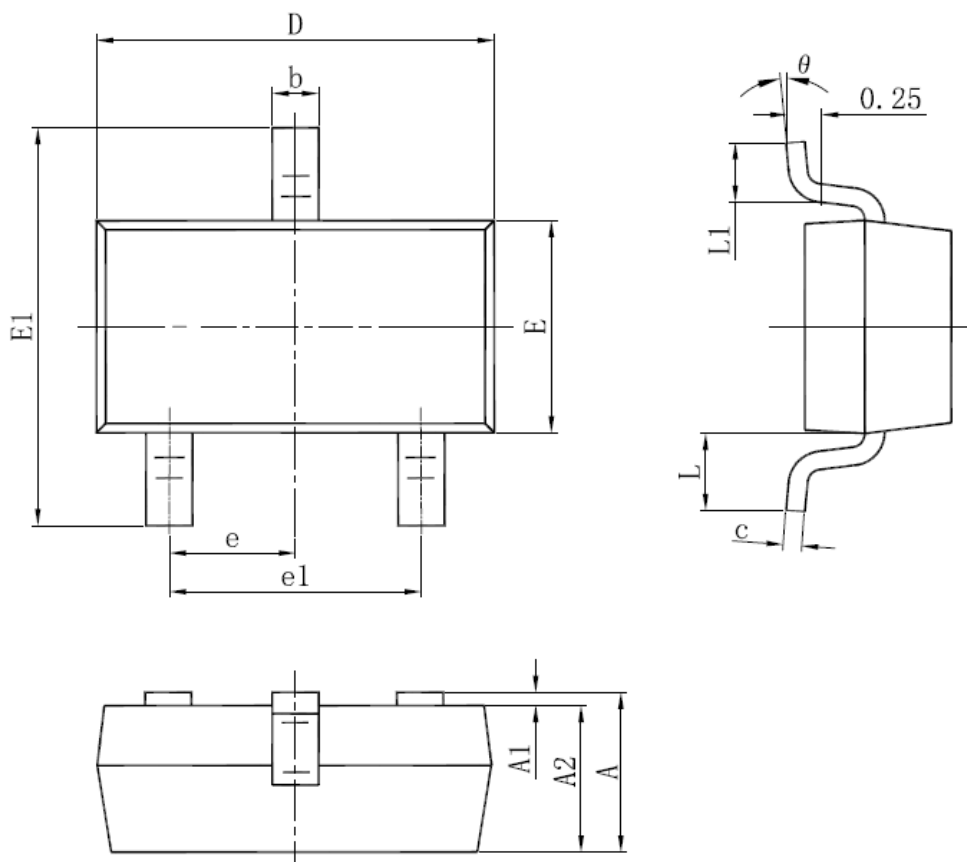
X =Assembly site code

Y =Year

WW =Work Week

Package Information

SOT-23



SYMBOL	MM		INCH		SYMBOL	MM		INCH	
	MIN	MAX	MIN	MAX		MIN	MAX	MIN	MAX
A	0.900	1.150	0.035	0.045	E1	2.250	2.550	0.089	0.100
A1	0.000	0.100	0.000	0.004	e	0.950 TYP.		0.037 TYP.	
A2	0.900	1.050	0.035	0.041	e1	1.800	2.000	0.071	0.079
b	0.300	0.500	0.012	0.020	L	0.550 REF.		0.022 REF.	
c	0.080	0.150	0.003	0.006	L1	0.300	0.500	0.012	0.020
D	2.800	3.000	0.110	0.118	θ	0°	8°	0°	8°
E	1.200	1.400	0.047	0.055					

ALL DIMENSIONS REFER TO JEDEC STANDARD
DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS

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